Products & Services

Applications

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Support

POWER DISCRETES & MODULES

- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ► Power MOSFET
- ▶ Silicon Carbide (SiC) Semiconductor
- ▶ Power Modules
- ▶ BJT (BiPolar Junction Transistor)
- BJT Modules (Power Integrated Circuit, PIC)
- Darlington Transistors
- Darlington Transistor Array
- NPN PNP Complimentary Transistor
- NPN Transistor
- PNP Transistor
- ▶ Legacy Power Discretes & Modules
- ▶ Diode and Rectifier Devices



The 2N4957UB is a military qualified silicon PNP amplifier transistor designed for VHF-UHF equipment and other high-reliability applications. Common applications include high gain low noise amplifier; oscillator, and mixer applications. It is also available in a low-profile TO-72 leaded package.

Package Carrier:

Waffle Pack

Electrical Rating	Symbol	Min	Тур	Max	Unit
DC Current Gain	HFE	30		165	
			-		
Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector Current (dc)	I _C			0.03	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			30	V
Junction Temperature (°C)	T_J			200	°C

Alphanumeric Parameter	Value
Quality Level	JANTX

This part can be found in the following product categories:

- Power Discretes & Modules BJT (BiPolar Junction Transistor) PNP Transistor
- Power Discretes & Modules BJT (BiPolar Junction Transistor)

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